

	Type	L #	Hits	Search Text
1	BRS	L1	20	(porous\$4 same (sio? or "sio.sub.2" or oxide) same (cvd or chemical adj vapor) same teos same ("o.sub.3" or ozone)) not taiwan-semiconductor-\$.as.
2	BRS	L2	1249114	sio? or "sio.sub.2" or oxide
3	BRS	L3	16727	2 near4 silane or "sih.sub.4"
4	BRS	L4	6	1 and 3
5	BRS	L5	4525	2 near4 silane or "sih.sub.4" near8 thermal near4 deposit\$4
6	BRS	L6	0	1 and 5
7	BRS	L7	4928	2 near4 silane or "sih.sub.4" same thermal near8 (deposit\$4 or grow\$4)
8	BRS	L9	0	1 and 7

	DBs
1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text
9	BRS	L10	100	2 near4 (silane or "sih.sub.4") same thermal near8 (deposit\$4 or grow\$4)
10	BRS	L11	974	((sio? or "sio.sub.2" or oxide) same (cvd or chemical adj vapor) same teos same ("o.sub.3" or ozone)) not taiwan-semiconductor-\$.as.
11	BRS	L12	6	11 and 10
12	BRS	L13	6	12 not 4
13	IS&R	L14	596	((438/788) or (438/790) or (438/771)).CCLS.

	DBs
9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	USPAT